



LOW POWER NPN SILICON TRANSISTOR

Qualified per MIL-PRF-19500/391

Qualified Levels:
JAN, JANTX,
JANTXV, and JANS

DESCRIPTION

This 2N3057A NPN leaded silicon transistor device is military qualified for high-reliability applications. Microsemi also offers numerous other transistor products to meet higher and lower power ratings with various switching speed requirements in both through-hole and surface-mount packages.

Important: For the latest information, visit our website <http://www.microsemi.com>.

FEATURES

- JEDEC registered 2N3057 number.
- JAN, JANTX, JANTXV and JANS qualifications are available per MIL-PRF-19500/391.
- Rad hard levels are also available per MIL-PRF-19500/391.
(For RHA datasheet see [JANS D2N3057A](#).)
- RoHS compliant by design.

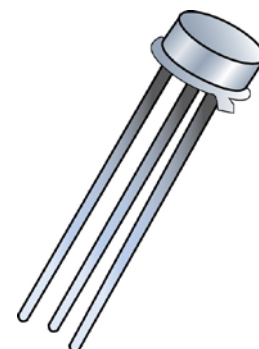
APPLICATIONS / BENEFITS

- Low profile metal TO-46 leaded package.
- Light weight.
- General-purpose switching and amplifier applications.
- Military and high-reliability applications.

MAXIMUM RATINGS @ $T_A = +25^\circ\text{C}$ unless otherwise noted.

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	T _J and T _{STG}	-65 to +200	°C
Thermal Impedance Junction-to-Ambient	R _{ΘJA}	325	°C/W
Thermal Impedance Junction-to-Case	R _{ΘJC}	80	°C/W
Collector-Emitter Voltage	V _{CEO}	80	V
Collector-Base Voltage	V _{CBO}	140	V
Emitter-Base Voltage	V _{EBO}	7.0	V
Collector Current	I _C	1.0	A
Total Power Dissipation:	P _D	@ T _A = +25 °C ⁽¹⁾	0.5
		@ T _C = +25 °C ⁽²⁾	1.8
			W

Notes: 1. Derate linearly 2.3 mW/ $^\circ\text{C}$ for $T_A \geq +25^\circ\text{C}$.
2. Derate linearly 10.3 mW/ $^\circ\text{C}$ for $T_C \geq +25^\circ\text{C}$.



**TO-46 (TO-206AB)
Package**

Also available in:

TO-39 (TO-205AD)
(short-leaded)
 [2N3019S](#)

TO-5 package
(long-leaded)
 [2N3019](#)

TO-18 (TO-206AA)
(leaded)
 [2N3700](#)

UB package
(surface mount)
 [2N3700UB](#)

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MECHANICAL and PACKAGING

- CASE: Low profile nickel cap.
- TERMINALS: Gold over nickel plated kovar leads. Solder dip (Sn63/Pb37) available upon request. NOTE: Solder dip will eliminate RoHS compliance.
- MARKING: Part number, date code, manufacturer's ID and serial number.
- WEIGHT: Approximately 0.234 grams.
- See [Package Dimensions](#) on last page.

PART NOMENCLATURE**JAN****2N3057A****Reliability Level**

JAN = JAN level
JANTX = JANTX level
JANTXV = JANTXV level
JANS = JANS level
Blank = Commercial

JEDEC type number

(see [Electrical Characteristics](#) table)

SYMBOLS & DEFINITIONS

Symbol	Definition
f	Frequency
I _B	Base current (dc)
I _E	Emitter current (dc)
T _A	Ambient temperature
T _C	Case temperature
V _{CB}	Collector to base voltage (dc)
V _{CE}	Collector to emitter voltage (dc)
V _{EB}	Emitter to base voltage (dc)

ELECTRICAL CHARACTERISTICS @ $T_A = +25\text{ }^{\circ}\text{C}$, unless otherwise noted

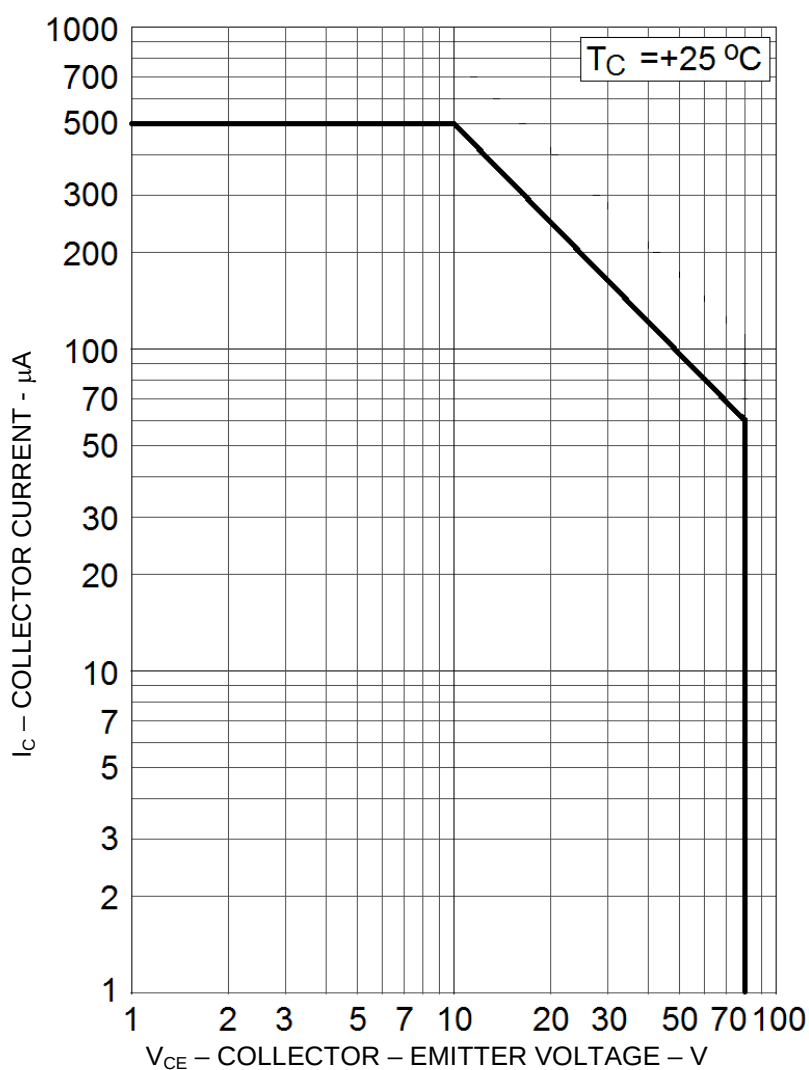
Parameters / Test Conditions	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Current $I_C = 30\text{ mA}$	$V_{(BR)CEO}$	80		V
Collector-Base Cutoff Current $V_{CB} = 140\text{ V}$	I_{CBO}		10	μA
Emitter-Base Cutoff Current $V_{EB} = 7\text{ V}$	I_{EBO1}		10	μA
Collector-Emitter Cutoff Current $V_{CE} = 90\text{ V}$	I_{CES}		10	ηA
Emitter-Base Cutoff Current $V_{EB} = 5.0\text{ V}$	I_{EBO2}		10	ηA
ON CHARACTERISTICS				
Forward-Current Transfer Ratio $I_C = 150\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 0.1\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 10\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 500\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 1.0\text{ A}, V_{CE} = 10\text{ V}$	h_{FE}	100 50 90 50 15	300 300 300 300	
Collector-Emitter Saturation Voltage $I_C = 150\text{ mA}, I_B = 15\text{ mA}$ $I_C = 500\text{ mA}, I_B = 50\text{ mA}$	$V_{CE(sat)}$		0.2 0.5	V
Base-Emitter Saturation Voltage $I_C = 150\text{ mA}, I_B = 15\text{ mA}$	$V_{BE(sat)}$		1.1	V

DYNAMIC CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 1.0\text{ mA}, V_{CE} = 5.0\text{ V}, f = 1.0\text{ kHz}$	h_{fe}	80	400	
Magnitude of Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 50\text{ mA}, V_{CE} = 10\text{ V}, f = 20\text{ MHz}$	$ h_{fe} $	5.0	20	
Output Capacitance $V_{CB} = 10\text{ V}, I_E = 0, 100\text{ kHz} \leq f \leq 1.0\text{ MHz}$	C_{obo}		12	pF
Input Capacitance $V_{EB} = 0.5\text{ V}, I_C = 0, 100\text{ kHz} \leq f \leq 1.0\text{ MHz}$	C_{ibo}		60	pF

ELECTRICAL CHARACTERISTICS @ $T_A = +25\text{ }^{\circ}\text{C}$, unless otherwise noted (continued)
SAFE OPERATION AREA (See SOA graph below and [MIL-STD-750, method 3053](#))

DC Tests
 $T_C = 25\text{ }^{\circ}\text{C}$, 1 cycle, $t = 10\text{ ms}$
Test 1
 $V_{CE} = 10\text{ V}$
 $I_C = 180\text{ mA}$
Test 2
 $V_{CE} = 40\text{ V}$
 $I_C = 45\text{ mA}$
Test 3
 $V_{CE} = 80\text{ V}$
 $I_C = 22.5\text{ mA}$

(1) Pulse Test: Pulse Width = $300\text{ }\mu\text{s}$, duty cycle $\leq 2.0\%$.

Maximum Safe Operating Area

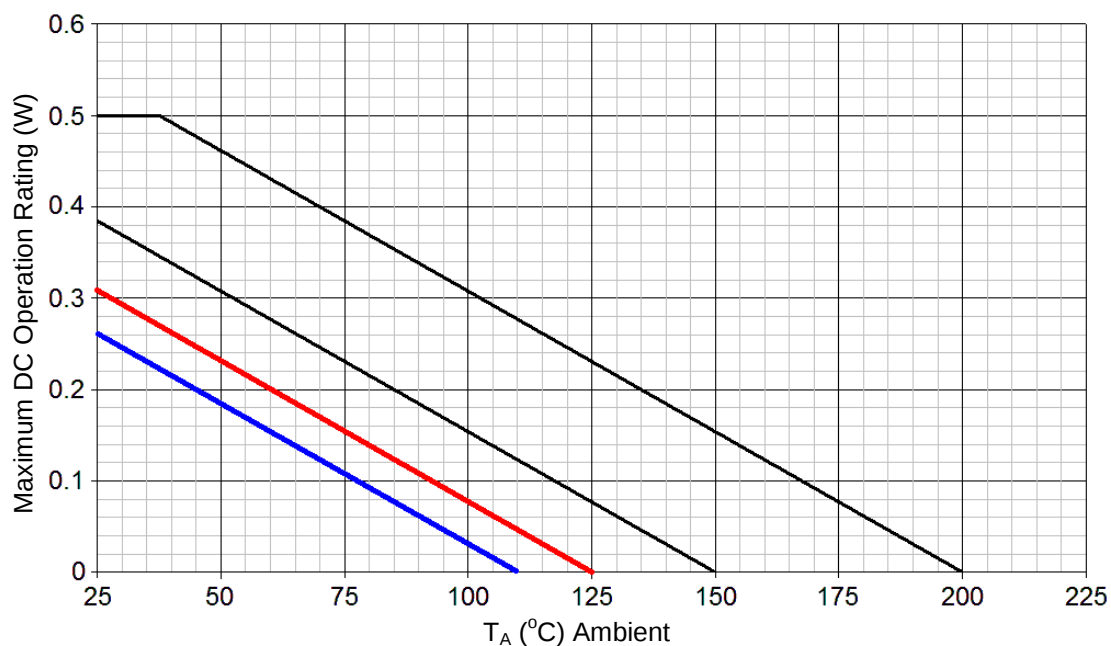
GRAPHS


FIGURE 1
Temperature-Power Derating (R_{θJA})
 Leads = .125 inch (3.175mm)

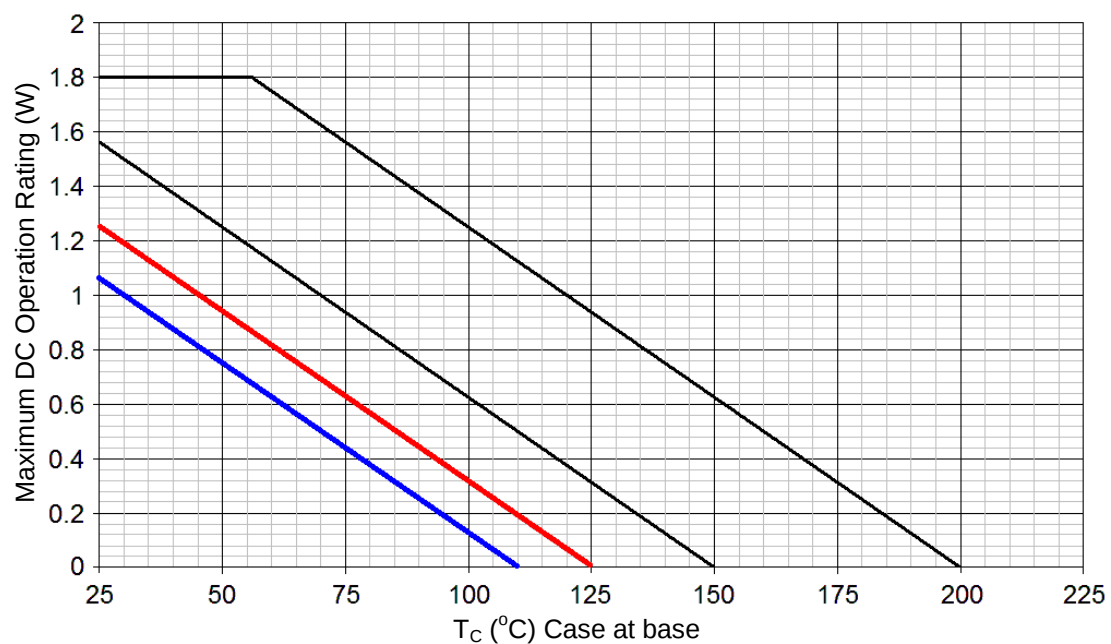
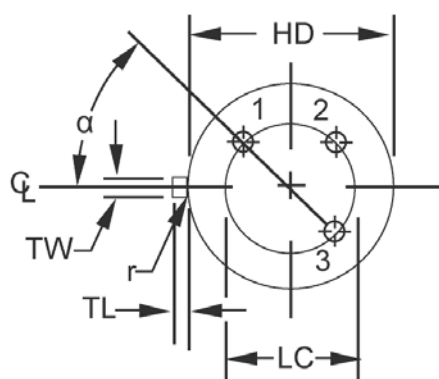
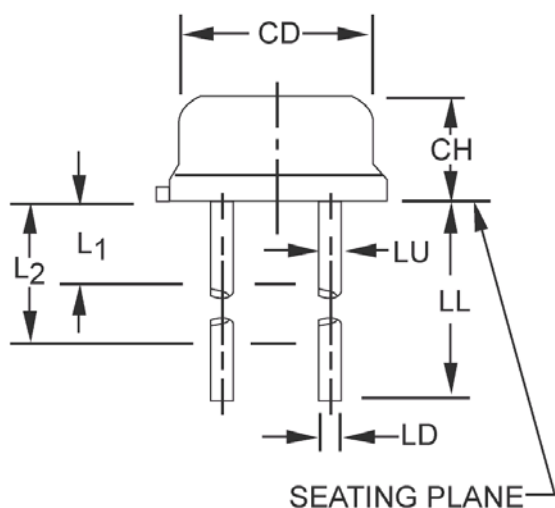


FIGURE 2
Temperature-Power Derating (R_{θJC})

PACKAGE DIMENSIONS


Symbol	Dimensions				Note
	Inches		Millimeters		
	Min	Max	Min	Max	
CD	.178	.195	4.52	4.95	
CH	.065	.085	1.65	2.16	
HD	.209	.230	5.31	5.84	
LC	.100 TP		2.54 TP		6
LD	.016	.021	0.41	0.53	7
LL	.500	1.750	12.70	44.45	7
LU	.016	.019	0.41	0.48	7
L1		.050		1.27	7
L2	.250		6.35		7
TL	.028	.048	0.71	1.22	3
TW	.036	.046	0.91	1.17	2
r	-	.007	-	0.18	10, 11
α	45° TP		45° TP		6

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Beyond r (radius) maximum, TW shall be held for a minimum length of .011 inch (0.28 mm).
4. Dimension TL measured from maximum HD.
5. Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC. This device may be measured by direct methods.
6. Dimension LU applies between L₁ and L₂. Dimension LD applies between L₂ and LL minimum. Diameter is uncontrolled in L₁ and beyond LL minimum.
7. All three leads.
8. The collector shall be internally connected to the case.
9. Dimension r (radius) applies to both inside corners of tab.
10. In accordance with ASME Y14.5M, diameters are equivalent to Φ x symbology.
11. Lead 1 = emitter, lead 2 = base, lead 3 = collector.

Данный компонент на территории Российской Федерации

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<http://moschip.ru/get-element>

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Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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